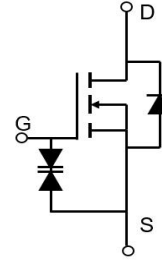


Description

Features

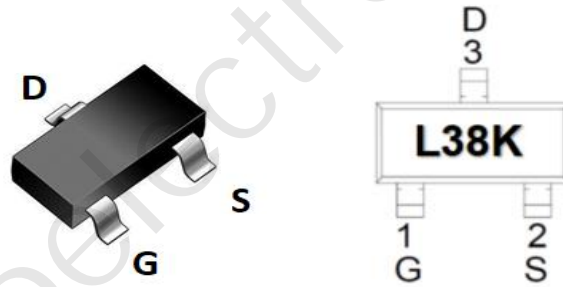
- 60V, 0.2A
 $R_{DS(ON)}$ Typ = 1.75Ω @ $V_{GS} = 10V$
 $R_{DS(ON)}$ Typ = 1.9Ω @ $V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free
- ESD Protected: 2KV



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

| Device | Marking | Package | Outline | Reel Size | Reel (pcs) | Per Carton (pcs) |
|-------------|---------|------------|---------|-----------|------------|------------------|
| CRMLCTL138K | L38K | SOT-523-3L | TAPING | 7" | 3000 | 120000 |

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Value | Units | |
|-----------------------------------|--|------------------------|-------|---|
| V _{DS} | Drain-to-Source Voltage | 60 | V | |
| V _{GS} | Gate-to-Source Voltage | ±20 | V | |
| I _D | Continuous Drain Current | T _A = 25°C | 0.2 | A |
| | | T _A = 100°C | 0.12 | A |
| I _{DM} | Pulsed Drain Current ⁽¹⁾ | 0.8 | A | |
| P _D | Power Dissipation | T _A = 25°C | 0.17 | W |
| R _{θJA} | Thermal Resistance, Junction to Ambient ⁽²⁾ | 735 | °C/W | |
| T _J , T _{STG} | Junction & Storage Temperature Range | -55 to 150 | °C | |

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|------------|------|------|------|------|
|--------|-----------|------------|------|------|------|------|

Off Characteristics

| | | | | | | |
|---------------|---------------------------------|---|----|---|----------|---------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ | 60 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$ | - | - | 1.0 | μA |
| I_{GSS} | Gate-Body Leakage Current | $V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$ | - | - | ± 10 | μA |

On Characteristics

| | | | | | | |
|--------------|--|---|-----|------|-----|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ | 0.7 | 1.1 | 1.5 | V |
| $R_{DS(ON)}$ | Static Drain-Source ON-Resistance ⁽³⁾ | $V_{GS} = 10\text{V}, I_D = 0.2\text{A}$ | - | 1.75 | 2.1 | Ω |
| | | $V_{GS} = 4.5\text{V}, I_D = 0.1\text{A}$ | - | 1.9 | 2.3 | Ω |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|---|-----|---|----|
| C_{iss} | Input Capacitance | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V},$ $f = 1\text{MHz}$ | - | 22 | - | pF |
| C_{oss} | Output Capacitance | | - | 3.4 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 2.3 | - | pF |
| Q_g | Total Gate Charge | $V_{GS} = 0 \text{ to } 4.5\text{V}$ $V_{DS} = 10\text{V}, I_D = 0.2\text{A}$ | - | 1.6 | - | nC |
| Q_{gs} | Gate Source Charge | | - | 0.2 | - | nC |
| Q_{gd} | Gate Drain("Miller") Charge | | - | 0.5 | - | nC |

Switching Characteristics

| | | | | | | |
|--------------|--------------------|---|---|----|---|----|
| $t_{d(on)}$ | Turn-On DelayTime | $V_{GS} = 10\text{V}, V_{DD} = 10\text{V}$ $I_D = 0.2\text{A}, R_{GEN} = 10\Omega$ | - | 2 | - | ns |
| t_r | Turn-On Rise Time | | - | 14 | - | ns |
| $t_{d(off)}$ | Turn-Off DelayTime | | - | 6 | - | ns |
| t_f | Turn-Off Fall Time | | - | 19 | - | ns |

Drain-Source Diode Characteristics and Max Ratings

| | | | | | | |
|----------|--|---|---|---|-----|---|
| I_S | Maximum Continuous Drain to Source Diode Forward Current | $V_{GS} = 0\text{V}, I_S = 0.2\text{A}$ | - | - | 0.2 | A |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 0.8 | A |
| V_{SD} | Drain to Source Diode Forward Voltage | | - | - | 1.2 | V |

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

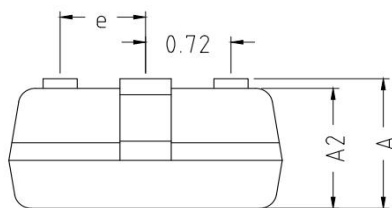
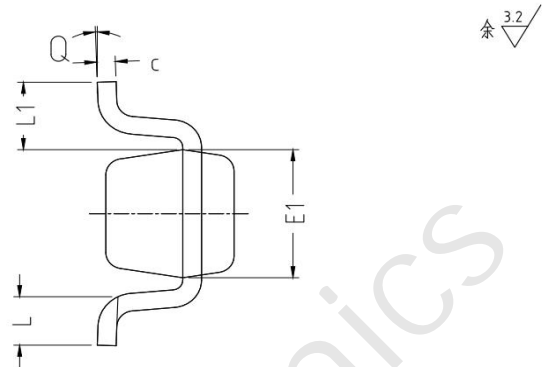
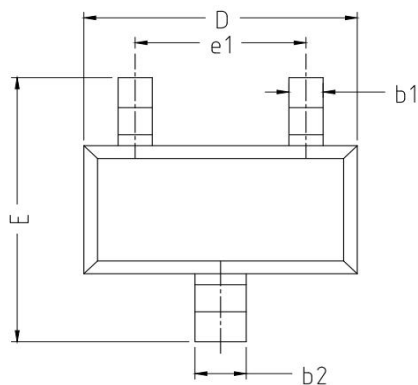


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform



Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-523-3L)




| COMMON IN DIMENSION (MM) | | | |
|--------------------------|-----------|-------|-------|
| PKG | SOT-523 | | |
| Symbol | MIN | MON | MAX |
| A | 0.700 | 0.800 | 0.900 |
| A1 | 0.000 | 0.050 | 0.100 |
| A2 | 0.700 | 0.750 | 0.800 |
| b1 | 0.150 | 0.200 | 0.250 |
| b2 | 0.250 | 0.300 | 0.350 |
| c | 0.100 | 0.130 | 0.200 |
| D | 1.550 | 1.600 | 1.700 |
| E | 1.450 | 1.600 | 1.750 |
| E1 | 0.700 | 0.800 | 0.900 |
| e | 0.500 TYP | | |
| e1 | 0.900 | 1.000 | 1.100 |
| L | 0.260 | 0.360 | 0.460 |
| L1 | 0.400REF | | |
| Q | 0° | 4° | 8° |

Important Notice

The information presented in datasheets is for reference only. CRM reserves the right to make changes at any time to any products or information herein, without notice.

Customers are responsible for the design and applications, including compliance with all laws, regulations and safety requirements or standards.

“Typical” parameters which provided in datasheets can vary in different applications and actual performance may vary over time. Customers are responsible for doing all necessary testing to minimize the risks associated with their applications and products.

 is a registered trademark of Wuxi CRM Microelectronics Co. , Ltd.

Copyright ©2023 CRM Microelectronics Co. , Ltd. All rights reserved.

Contact information

For more information, please visit: <http://www.crm-semi.tech>

For sales information, please send an email to: sales@crm-semi.com